

Supporting Information

High-sensitivity temperature sensing in $\text{MgGa}_2\text{O}_4:\text{Bi}^{3+}$ phosphors via thermal-assisted energy transfer

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Figure Captions:

Fig. S1 SEM spectra of MgGa_2O_4 : x% Bi^{3+} sample.

Fig. S2 Rietveld XRD refinements of the prepared MgGa_2O_4 :1.5% Bi^{3+} phosphors.

Fig. S3. XPS spectra of MgGa_2O_4 : 1.5% Bi^{3+} material.

Fig.S4: PLE and PL spectra of MgGa_2O_4 : 0% Bi^{3+} sample, $\lambda_{\text{em}} = 408, 502\text{nm}$ and $\lambda_{\text{ex}} = 250\text{nm}$;

Fig.S5: PLE spectra of MgGa_2O_4 : Bi^{3+} (0% ,1.5%) sample, $\lambda_{\text{em}} = 502\text{nm}$;

Fig. S6 Multipeak fitting of TL curves for MgGa_2O_4 : x% Bi materials with x equals to 0.75%, 1.5%, 3% and 5% Bi^{3+} , respectively.

Table S1 Rietveld refined crystallographic data for MgGa_2O_4 : 1.5% Bi

Table S2 Atomic occupancy, atomic fraction coordinates, and isotropic temperature factors for MgGa_2O_4 :1.5% Bi samples.

Table S3 Thermoluminescence kinetic parameters of MgGa_2O_4 :x% Bi^{3+} (x = 0.75, 1.5, 3, 5) samples.

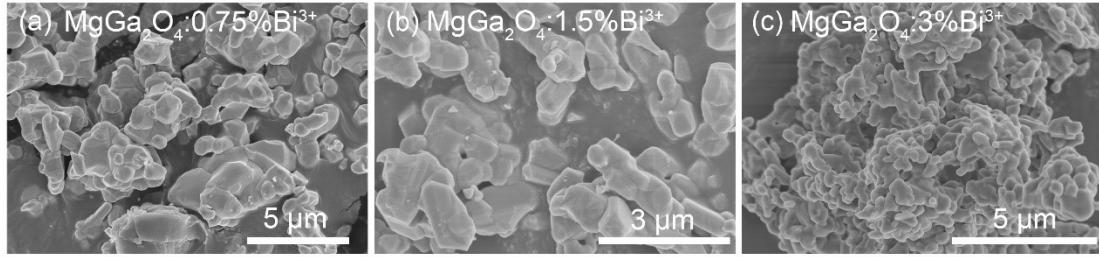


Fig. S1 SEM spectra of MgGa_2O_4 : $x\% \text{Bi}^{3+}$ sample, (a) $x=0.75$, (b) $x=1.5$, (c) $x=3$.

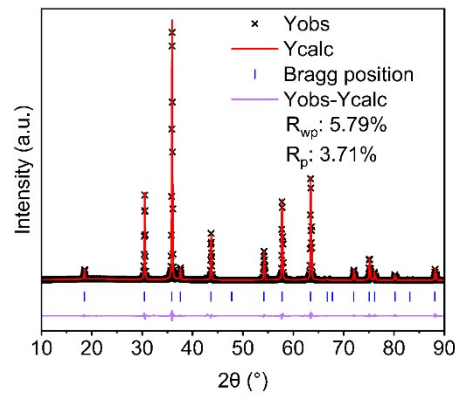


Fig. S2. Rietveld XRD refinements of the prepared MgGa_2O_4 : $1.5\% \text{Bi}^{3+}$ phosphors.

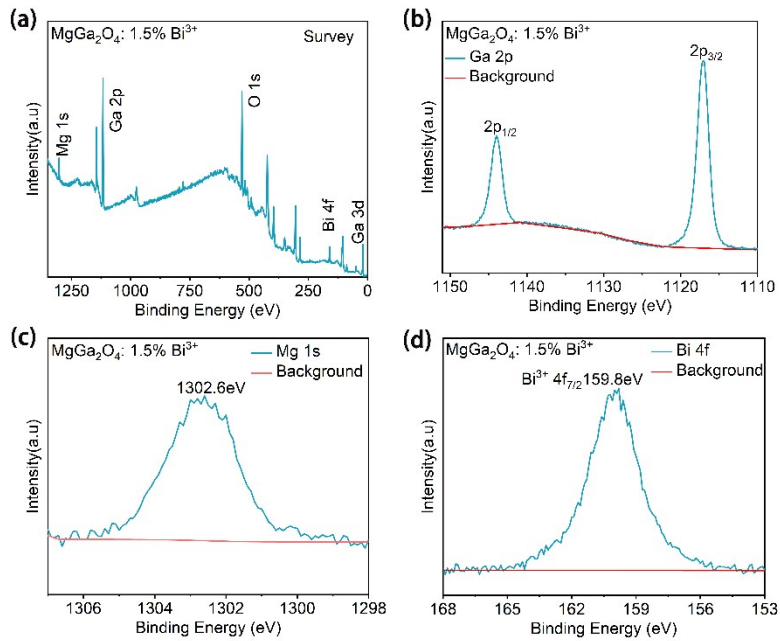


Fig. S3 XPS spectra of MgGa_2O_4 : $1.5\% \text{Bi}^{3+}$ material: (a) Survey, (b) Ga 2p, (c) Mg 1s, and (d) Bi 4f,

respectively.

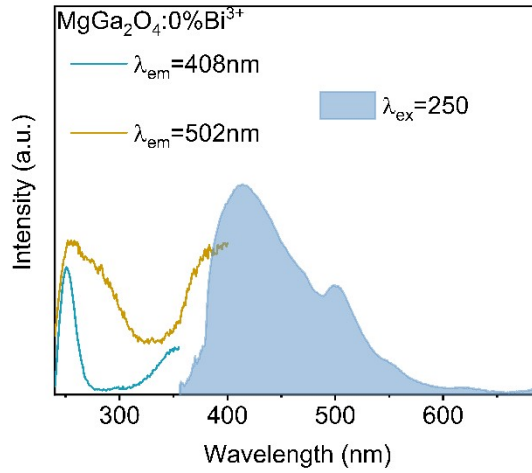


Fig.S4: PLE and PL spectra of $\text{MgGa}_2\text{O}_4: 0\% \text{Bi}^{3+}$ sample, $\lambda_{\text{em}} = 408, 502 \text{ nm}$ and $\lambda_{\text{ex}} = 250\text{nm}$;

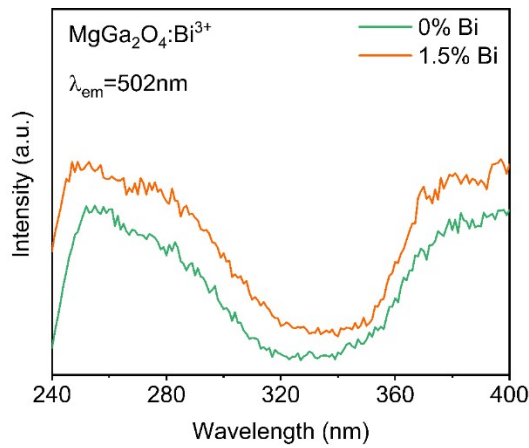


Fig.S5: PLE spectra of $\text{MgGa}_2\text{O}_4: \text{Bi}^{3+}(0\%, 1.5\%)$ sample, $\lambda_{\text{em}} = 502\text{nm}$;

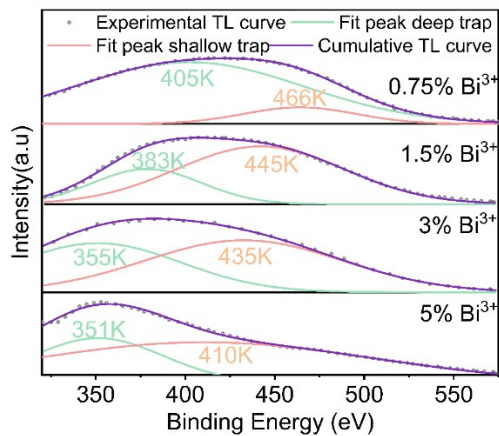


Fig. S6 Multiplex fitting of TL curves for $\text{MgGa}_2\text{O}_4: x\% \text{Bi}$ materials with x equals to 0.75%, 1.5%, 3% and 5% Bi^{3+} , respectively.

Table S1 Rietveld refined crystallographic data for MgGa₂O₄: 1.5% Bi

Parameters	Values
Crystal system	Cubic
Space group	Fd-3m (227)
a (Å) = b (Å) = c (Å)	8.29159(9)
α (°) = β (°) = γ (°)	90
Volume (Å ³)	570.05
Z	8
R _p	3.71%
R _{wp}	5.79%
Rc	1.55%
X ²	3.54

Table S2 Atomic occupancy, atomic fraction coordinates, and isotropic temperature factors for MgGa₂O₄:1.5% Bi samples.

Atom	Wyck.	s.o.f.	x	y	z	B/ 10⁴ pm²
O1	32e	1.000000	0.243249	0.243249	0.243249	0.515000
MG1	16c	0.492449	0.000000	0.000000	0.000000	0.352000
GA1	16c	0.488024	0.000000	0.000000	0.000000	0.352000
GA2	8b	0.796505	0.375000	0.375000	0.375000	0.317000
MG2	8b	0.200000	0.375000	0.375000	0.375000	0.317000
Bi1	16c	0.019527	0.000000	0.000000	0.000000	0.352000

Atom	Wyck.	s.o.f.	x	y	z	B/ 10 ⁴ pm ²
Bi2	8b	0.009750	0.375000	0.375000	0.375000	0.317000

Table S3 Thermoluminescence kinetic parameters of MgGa₂O₄:x%Bi³⁺ (x = 0.75, 1.5, 3, 5) samples.

Sample	Deconvoluted TL peaks	Max. tem. peak (Tm)	Activation energy (eV)
MgGa ₂ O ₄ :0.75%Bi ³⁺	Peak1	405K	0.810
	Peak2	466K	0.932
MgGa ₂ O ₄ :1.5%Bi ³⁺	Peak1	383K	0.766
	Peak2	445K	0.890
MgGa ₂ O ₄ :3%Bi ³⁺	Peak1	355K	0.710
	Peak2	435K	0.870
MgGa ₂ O ₄ :5%Bi ³⁺	Peak1	351K	0.702
	Peak2	410K	0.820